

ABSTRACT OF THE DISCLOSURE

A method of forming a bit line contact via. The method includes providing a substrate having a transistor with a gate electrode, drain region, and source region, forming a
5 conductive layer overlying the drain region, conformally forming an insulating barrier layer overlying the substrate, blanketly forming a dielectric layer overlying the insulating barrier layer, and forming a via through the dielectric layer and insulating barrier layer, exposing the
10 conductive layer.